

Single-Event-Effect Test Report

R6, 200V, N-Channel

August 2003

International
IOR Rectifier

HI-REL PRODUCTS

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INTRODUCTION

On June 20th and August 25th, 2003 International Rectifier Corp. (IR) tested several product types for Single Event Effects (SEE) hardness. The irradiation was performed at Texas A & M University, using the K500 Superconducting Cyclotron. The Xenon (Xe) and Gold (Au) ion species with three (3) different combinations of Energy, Range and Linear-Energy-Transfer (LET) levels was used to characterize and verify the SEE hardness of each product type. The product types submitted for evaluation and this report are included in Table 1 below:

Table 1 Product Types Tested

Product Type	BVDSS Rating	Gen. / Channel / Process	Wafer Lot
IRH67260	200 Volts	R6 / N / 200 Volts	ER33831
IRH67260	200 Volts	R6 / N / 200 Volts	ER34312
IRH67230	200 Volts	R6 / N / 200 Volts	ER34181

The wafer lots noted above are the lots from which the test samples originated. For each product type, the results of testing herein are applicable to all other wafer lots having the same design and process.

Additionally, Mr. Louis Jaquish of Defense Supply Center Columbus (DSCC-VQE) has performed an audit of IR for the purpose of assigning lab suitability and has granted IR a Letter of Lab Suitability for Test Method 1080 in June 1998.

TEST METHOD

The test method used as a guide in developing the test plan is MIL-STD-750, Test Method 1080. The test method establishes the basic requirements for the performance of the test. Additionally, DSCC has established a minimum acceptance level of three (3) devices for each insitu bias condition. Test method 1080, in conjunction with DSCC requirements, was utilized to write the test plan.

TEST PLAN and PROCEDURE

The test plan is included in Appendix C. In summary, the testing occurred in the following manner: All devices / test samples were built and electrically tested in TO-3 packages. The lid was removed from each test sample at the test site or the samples were produced without the lid. Up to 18 test samples were loaded onto the test board and placed into the beam line, under high vacuum conditions. The desired test sample was positioned into the beam line, and when ready the beam shutter was removed beginning the irradiation of the test sample. Once the desired fluence was achieved the beam was automatically shuttered and the bias removed. The biasing equipment then subjected the test samples to gate stresses up to 20V.

The Ion with its LET and Energy must be selected for a Range of at least twice the depletion depth of the die under test.

TEST FACILITY

The K500 Superconducting Cyclotron is equipped with the necessary dosimetry to ensure the ion beam is meeting the customer expectation. A printout of the runs, included in Appendix B, also includes the beam parameters, i.e., LET, energy, Range, etc., for each run. Table 2 summarizes the 3 beam criteria for the ion species properly selected and utilized.

Table 2. Ion Beam Criteria

Ion	LET MeV/(mg/cm²)	Energy MeV	Range μm
Xe	43	2441	205
Xe	59	825	66
Au	90	1480	80

The fluence and flux specified for this test was 3E5 ions/cm² and 1E4 ions/cm²/sec, respectively. The beam diameter was set to cover the whole die-attachment area. The angle of incidence was set to zero (normal to the die surface).

RESULTS

The insitu bias conditions, where 0 failures occurred for each product type, are shown in Table 3. These results are shown graphically in Figure 1 as a plot of the Safe Operation Area (SOA). Each point on the graph, or insitu bias condition, has been verified by irradiating and subsequent electrical testing of a minimum of 3 devices, with no valid failures allowed. The devices were returned to IR and tested using production ATE. The results of the test were inspected and matched to the notes taken during the test, see Appendix F. The post-irradiation data correlates with the expected test results.

It should be noted that acceptance is assumed for product types operating at conditions below those tested herein. For example the IRH67260 was not tested under the VGS bias conditions of 0V through -5V with the Xe ion of LET=59 MeV/(mg/cm²). The test engineer made a calculated risk assessment based on SEE Process History & SEE results at lower LET and chose to begin characterization and verification at VGS = -10V. The insitu acceptance at the -10V was then extended to the lower VGS bias voltages.

Furthermore the extension of more stressful conditions to less stressful conditions shall also apply to the LET conditions of the various ion species. For example successful operation using the Au ion (LET of 90 MeV/(mg/cm²)) shall also imply that any other ion with a LET < 90, shall also be acceptable and not require verification.

The different runs and respective test conditions are all tabulated in Appendices A and B. Table 4 may be used as an index to identify which runs apply to a specific product type with a specific ion. Unlisted Runs are not related to this report.

Table 3 Device Insitu Bias Conditions (VDS vs. VGS) with Ion Species

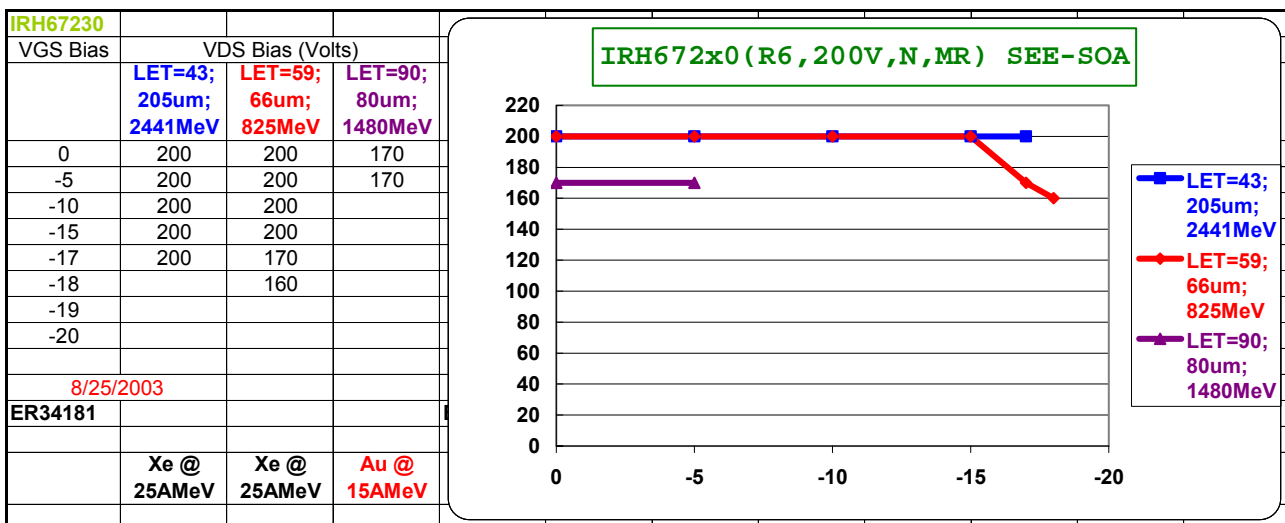
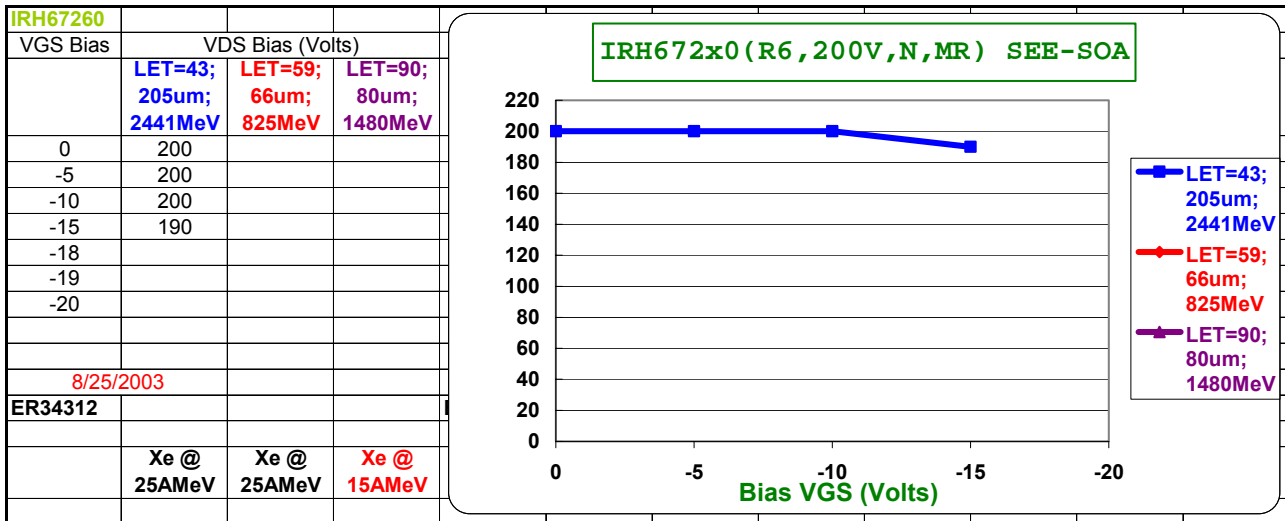
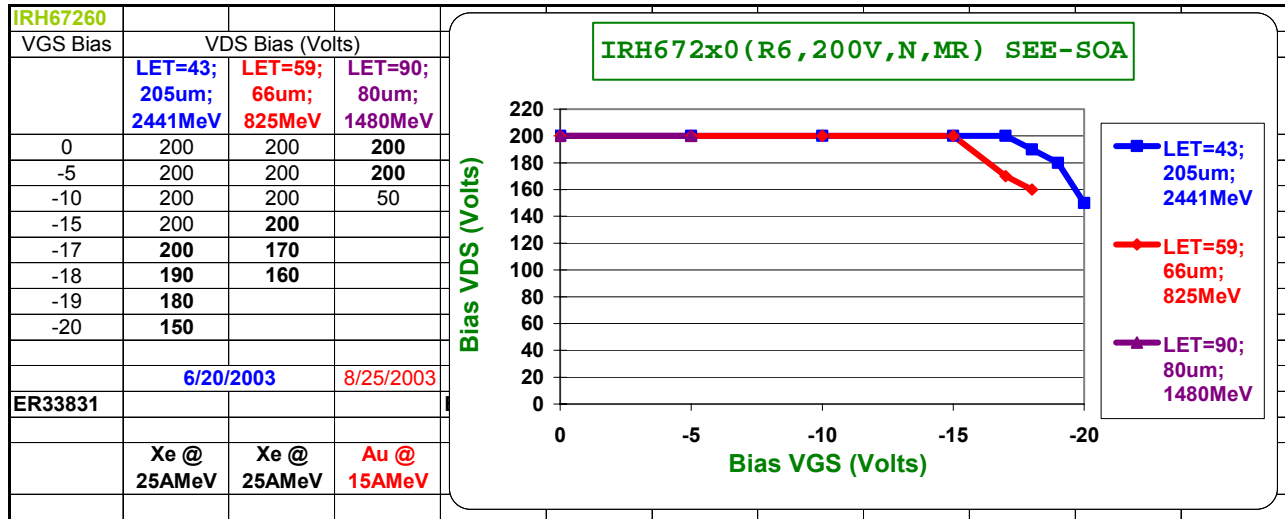
Device Type Part Number Wafer Lot	Ion (LET)	VGS=0V	VGS=-5V	VGS=-10V	VGS=-15V	VGS=-17V	VGS=-18V	VGS=-19V	VGS=-20V
IRH67260 (R6, 200Volts, N-Channel) ER33831	Xe (43)	Qualified	Qualified	Qualified	Qualified	200 V	190 V	180 V	150 V
	Xe (59)	Qualified	Qualified	Qualified	200 V	170 V	160 V		
	Au (90)	200 V	200 V						
IRH67260 (R6, 200Volts, N-Channel) ER34312	Xe (43)	Qualified	Qualified	200 V	190 V				
IRH67230 (R6, 200Volts, N-Channel) ER34181	Xe (43)	Qualified	Qualified	200 V	200 V	200 V			
	Xe (59)	Qualified	Qualified	200 V	200 V	170 V	160 V		
	Au (90)	170 V	170 V						

Note: “Qualified” indicates part is qualified by extension of insitu bias testing at higher VGS level. See Concluding Tutorial for more details.

Table 4 Run Number Index

Device Type / Part Number	Wafer Lot Number	Ion (LET)	Run Date	Run Number
IRH672x0 (R6, 200Volts, N-ch, MR)	ER33831	Xe (43)	06-20-2003	169 to 201
	ER33831	Xe (59)	06-20-2003	202 to 222
	ER34312	Xe (43)	08-25-2003	189 to 203
	ER34181	Xe (43)	08-25-2003	204 to 220
	ER34181	Xe (59)	08-25-2003	221 to 226
	ER33831	Au (90)	08-25-2003	227 to 236
	ER34312	Au (90)	08-25-2003	237 to 241
	ER34181	Au (90)	08-25-2003	242 to 263

Figure 1 Device Safe Operating Area



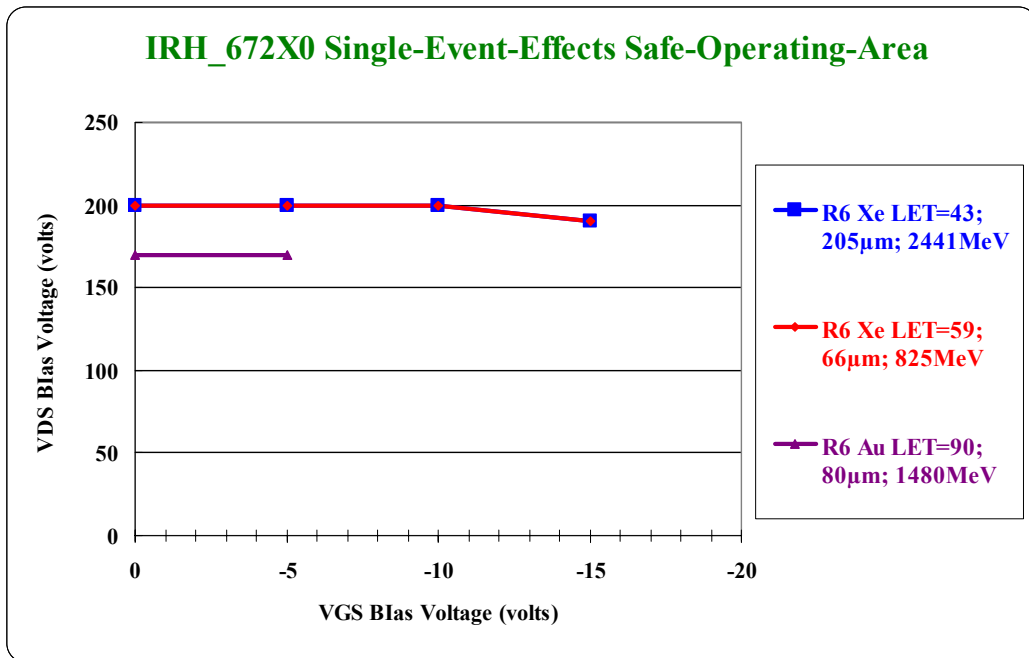
CONCLUSION

For a final SEE Specification, the SEE Results from all three wafer lots with two die sizes are combined as worst-case result and listed below in both tabular and graphic SEE Safe-Operating-Area. The 200-Volt N-Channel Dual-Epi R6 (IRHC671x0) is well SEE-hard against the charged Xenon (Xe) ion at 100% rated VDS and -10V VGS applied and against Gold heavy-ion at 85% rated VDS and -5V VGS applied.

FINAL Single-Event-Effect Safe Operating Area (Tabular)

Device Type Part Number	Ion (LET)	VGS=0V	VGS=-5V	VGS=-10V	VGS=-15V
IRH67260 (R6, 200Volts, N-Channel)	Xe (43)	Qualified	Qualified	200 V	190 V
	Xe (59)	Qualified	Qualified	200 V	190 V
	Au (90)	170 V	170 V		

FINAL Single-Event-Effect Safe Operating Area (Graph)



CONCLUDING TUTORIAL

The following is presented to help the reader understand the basis on which SEE Testing is extended to the other part numbers.

Extending Single Event Effects Testing

International Rectifier has designed Single Event Effects (SEE) experiments to maximize facility usage using four, industry accepted, assumptions as follows:

- I. Test results for one die size are representative of other die sizes, if the process and design rules are not changed. In other words the scaling of die size has no affect if all other variables are held constant. Please note that for a given voltage and technology, there are no differences in design and process for the various sizes of IR's radiation hardened MOSFET die, thus the assumption is valid. In reality, IR will always test the largest available die size. We consider this a worst-case scenario. The industry standard for acceptance of a given in-situ bias condition, is the acceptable performance of three or more devices at the specified conditions. Presently a supplier could achieve this standard with size 1 die thru size 6 die. We believe that use of the smaller die reduces the probability of failure, and thus reduces the chance of a SEE problem being discovered. The size 1 die are about one-twelfth the size of the size 6 die. Thus successfully testing three size 6 die is roughly equivalent to testing 36 size 1 die. This results in a savings of valuable test time at the SEE test facility, without degrading the final test result.
- II. Acceptable test results taken at given VGS and VDS conditions are applicable to lower VGS and VDS conditions. In other words an acceptable test result (≥ 3 devices passing) at VGS = -15V and VDS = 200V, would also apply to VGS = -10, -5 or 0V at the same or lower VDS condition. In several cases parts have been tested at the worst-case in-situ bias condition of VGS = -20V and VDS = max rated BVDSS. With acceptable test results, the safe operation area, has been extended from VGS = 0 to -20V and VDS from 0 to the max rating. It is not necessary to verify every point below the accepted in-situ bias conditions. Again this saves valuable experiment time.
- III. Acceptable test results taken with a given LET, would also apply at other lower LETs. It is generally accepted that successful test results with Iodine, for example, implies the device would be hard against Bromine, Krypton, Nickel, etc., ion species with a lower LET. It is not necessary to test at each lower LET, again saving valuable test time.
- IV. The package used has no effect on the SEE hardness of a die. The die are characterized fully exposed to the ion beam. In other words the lid of the package is removed making the die visible. This removes the package as a variable when comparing test results. As a rule IR uses the common TO3 package for mounting die for SEE tests.

Each of the assumptions above is generally accepted within the industry. IR has verified their validity over the last several years and makes appropriate use of them to maximize the benefit for our customers.

Appendix A

Log Sheets

(SEE Run Data)

International Rectifier
SEE Test Report
August 2003 – TAMU Cyclotron

Test Date	Run #	Ion	LET(Si) MeV.cm2/mg	Energy MeV	Range µm	Flux #/cm2/sec	Fluence #/cm2	Angle deg	BeamDia. cm.	Vacuum or Air	Device Type	Wafer Lot	Wafer No.	Serial No.	Batch No.	Socket No.	VGS Volts	VDS Volts	Pass/Fail Blank=Pass
200V, N, MR, R6 to Xeon (with LET=43)																			
6/20/2003	169	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-5	200	
6/20/2003	170	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-10	200	
6/20/2003	171	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	100	
6/20/2003	172	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	120	
6/20/2003	173	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	140	
6/20/2003	174	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	160	
6/20/2003	175	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	180	
6/20/2003	176	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-15	200	
6/20/2003	177	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-16	200	
6/20/2003	178	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-17	200	
6/20/2003	179	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-18	200	
6/20/2003	180	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	2	F1	1	-19	200	Failed
6/20/2003	181	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	3	F2	2	-18	200	
6/20/2003	182	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	4	F3	3	-18	200	
6/20/2003	183	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	5	F4	4	-18	200	Failed
6/20/2003	184	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	1	1	F5	5	-17	200	
6/20/2003	185	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	7	F6	6	-18	180	
6/20/2003	186	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	7	F6	6	-18	190	
6/20/2003	187	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	8	F7	7	-18	190	
6/20/2003	188	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	9	F8	8	-18	190	
6/20/2003	189	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	10	F9	9	-19	170	
6/20/2003	190	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	2	10	F9	9	-19	180	
6/20/2003	191	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	3	11	F10	10	-19	170	
6/20/2003	192	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	3	11	F10	10	-19	180	
6/20/2003	193	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	3	14	F12	12	-19	180	
6/20/2003	194	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	3	15	F13	13	-20	160	
6/20/2003	195	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	3	15	F13	13	-20	170	
6/20/2003	196	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	17	F15	15	-20	160	
6/20/2003	197	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	17	F15	15	-20	160	
6/20/2003	198	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	17	F15	15	-20	170	
6/20/2003	199	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	18	F16	16	-20	170	Failed
6/20/2003	200	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	19	F17	17	-20	160	Failed
6/20/2003	201	Xe	43	2441	205	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	4	20	F18	18	-20	150	
200V, N, MR, R6 to Xeon (with LET=59)																			
6/20/2003	202	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	27	F19	1	-5	200	
6/20/2003	203	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	27	F19	1	-10	200	
6/20/2003	204	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	27	F19	1	-15	200	
6/20/2003	205	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	27	F19	1	-17	200	
6/20/2003	206	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	28	F20	2	-15	200	
6/20/2003	207	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	28	F20	2	-17	200	Failed
6/20/2003	208	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	29	F21	3	-15	200	
6/20/2003	209	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	6	30	F22	4	-15	200	
6/20/2003	210	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	7	31	F23	5	-17	180	
6/20/2003	211	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	7	31	F23	5	-17	190	
6/20/2003	212	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	7	32	F24	6	-17	180	Failed
6/20/2003	213	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	7	33	F25	7	-17	170	
6/20/2003	214	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	7	33	F25	7	-18	160	
6/20/2003	215	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	36	F28	10	-18	160	
6/20/2003	216	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	36	F28	10	-17	170	
6/20/2003	217	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	37	F29	12	-17	170	
6/20/2003	218	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	37	F29	12	-18	160	
6/20/2003	219	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	38	F30	13	-19	140	Failed
6/20/2003	220	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	8	39	F31	15	-19	120	
6/20/2003	221	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	9	42	F33	17	-19	100	Failed
6/20/2003	222	Xe	59	825	66	1.0E+04	3.0E+05	0		vacuum	IRH67260	ER33831	9	44	F34	18	-19	80	Failed

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Test Date	Run #	Ion	LET(Si) MeV.cm2/mg	Energy MeV	Range µm	Flux #/cm2/sec	Fluence #/cm2	Angle deg	BeamDia. cm.	Vacuum or Air	Device Type	Wafer Lot	Wafer No.	Serial No.	Batch No.	Socket No.	VGS Volts	VDS Volts	Pass/Fail Blank=Pass
200V, N, MR, R6 to Xeon (with LET=43)																			
8/25/2003	189	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	1	1	G1	1	-5	200	
8/25/2003	190	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	1	1	G1	1	-10	200	
8/25/2003	191	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	1	1	G1	1	-15	200	Failed
8/25/2003	192	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	2	3	G2	2	-10	200	
8/25/2003	193	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	2	3	G2	2	-15	180	
8/25/2003	194	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	2	3	G2	2	-15	190	
8/25/2003	195	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	2	3	G2	2	-20	150	Failed
8/25/2003	196	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	3	5	G3	3	-20	100	Failed
8/25/2003	197	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	4	8	G4	4	-18	100	Failed
8/25/2003	198	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	5	9	G5	5	-18	50	
8/25/2003	199	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	5	9	G5	5	-18	60	
8/25/2003	200	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	5	9	G5	5	-18	70	
8/25/2003	201	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	5	9	G5	5	-18	80	
8/25/2003	202	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	5	9	G5	5	-18	90	
8/25/2003	203	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67260	ER34312	6	12	G6	6	-18	70	Failed
200V, N, MR, R6 to Xeon (with LET=43)																			
8/25/2003	204	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	1	1	H1	7	-10	200	
8/25/2003	205	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	1	1	H1	7	-15	100	
8/25/2003	206	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	1	1	H1	7	-15	150	Failed
8/25/2003	207	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	6	11	I1	13	-10	200	Invalid
8/25/2003	208	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-10	200	
8/25/2003	209	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	100	
8/25/2003	210	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	150	
8/25/2003	211	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	160	
8/25/2003	212	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	160	
8/25/2003	213	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	170	
8/25/2003	214	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	180	
8/25/2003	215	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	190	
8/25/2003	216	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-15	200	
8/25/2003	217	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-17	180	
8/25/2003	218	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-17	190	
8/25/2003	219	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-17	200	
8/25/2003	220	Xe	43	2441	205	1.0E+04	1.0E+05	0		Vacuum	IRH67230	ER34181A	8	15	I3	15	-18	180	Failed
200V, N, MR, R6 to Xeon (with LET=59)																			
8/25/2003	221	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-10	200	
8/25/2003	222	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-15	200	Invalid
8/25/2003	223	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-15	200	
8/25/2003	224	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-17	160	
8/25/2003	225	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-17	170	
8/25/2003	226	Xe	59	825	66	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	17	I4	16	-18	160	
200V, N, MR, R6 to Gold (with LET=90)																			
8/25/2003	227	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	10	48	J1	1	-5	100	
8/25/2003	228	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	10	48	J1	1	-5	150	
8/25/2003	229	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	10	48	J1	1	-5	200	
8/25/2003	230	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	10	48	J1	1	-10	100	Failed
8/25/2003	231	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	10	49	J2	2	-5	200	
8/25/2003	232	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	11	54	J3	3	-5	200	
8/25/2003	233	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	11	55	J4	4	-5	200	
8/25/2003	234	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	12	59	J5	5	-10	50	
8/25/2003	235	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	12	59	J5	5	-10	60	Failed
8/25/2003	236	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67260	ER33831	12	60	J6	6	-10	50	

International Rectifier
SEE Test Report
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Test Date	Run #	Ion	LET(Si) MeV.cm2/mg	Energy MeV	Range µm	Flux #/cm2/sec	Fluence #/cm2	Angle deg	BeamDia. cm.	Vacuum or Air	Device Type	Wafer Lot	Wafer No.	Serial No.	Batch No.	Socket No.	VGS Volts	VDS Volts	Pass/Fail Blank=Pass
200V, N, MR, R6 to Gold (with LET=90)																			
8/25/2003	242	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	21	42	H7	11	-5	100	Invalid
8/25/2003	243	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	100	
8/25/2003	244	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	110	
8/25/2003	245	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	120	
8/25/2003	246	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	130	
8/25/2003	247	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	140	
8/25/2003	248	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	150	
8/25/2003	249	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	22	43	H8	12	-5	160	Failed
8/25/2003	250	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	23	45	H9	13	-5	150	
8/25/2003	251	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	23	45	H9	13	-5	160	Failed
8/25/2003	252	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	150	
8/25/2003	253	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	160	
8/25/2003	254	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	170	
8/25/2003	255	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	180	
8/25/2003	256	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	190	
8/25/2003	257	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	6	12	I7	15	-5	200	Failed
8/25/2003	258	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	8	16	I8	16	-5	190	Failed
8/25/2003	259	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	18	I9	17	-5	160	
8/25/2003	260	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	18	I9	17	-5	170	
8/25/2003	261	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	9	18	I9	17	-5	180	
8/25/2003	262	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	10	20	I10	18	-5	170	
8/25/2003	263	Au	90	1480	80	1.0E+04	3.0E+05	0		Vacuum	IRH67230	ER34181A	10	20	I10	18	-5	180	

Appendix B

TAMU Cyclotron Institute

Facility Beam Data & Graphs

Appendix C

International Rectifier

Test Plan

and

Procedure

Test Plan, Single Event Effects (TAMU, K500 Superconducting Cyclotron)

1.0 Purpose

The purpose of this test is to characterize and establish Single Event Effects (SEE) Safe-Operating-Area (SOA) curves for several International Rectifier Corp. (IR) Power MOSFET devices. The data resulting from the tests shall be used for qualification to several US Government military slash sheets and shall be incorporated in the IR data sheets.

2.0 Test Responsibility

IR shall be responsible for conducting the tests, which shall be performed at the Texas A & M University (TAMU), Cyclotron Institute. IR shall be responsible for the SEE testing of devices-under-test (DUT) and final Test Report.

3.0 Test Facility

3.1 K500 Superconducting Cyclotron

The Texas A&M University, Tandem K500 Superconducting Cyclotron shall be used to provide the necessary ion species and energy. TAMU Cyclotron Institute shall provide adequate dosimeter for verification of the ion beam parameters.

3.2 Test Equipment

The necessary test equipment including the test interface board, cables, power supplies, etc. shall be provided by IR. IR shall provide the equipment needed to de-lid and handle the individual test devices.

4.0 Test Devices

4.1 The following device types are planned for characterization and qualification:

IRH67260	(Hex-6, 200V, N-channel, R6, MR Process)	Depletion Depth=38 μ m typical
IRH67230	(Hex-3, 200V, N-channel, R6, MR Process)	Depletion Depth=38 μ m typical

4.2 All devices shall be built in TO-3 packages. The devices shall be properly sealed and packed for transportation to TAMU Cyclotron Institute.

4.3 All devices shall be verified for correct electrical performance prior to arrival at TAMU Cyclotron.

5.0 Test Method

The MIL-STD-750, Method 1080 shall be used to set procedure for all testing described herein.

6.0 Ion Specie and Energy

There are three (3) available ion specie with different energy level, at BNL. All parts will be first tested with one specie of lowest energy (LET) level before the Accelerator is switched to the next ion specie with higher energy level.

a. Xeon	$_{54}\text{Xe}^{131}$	Energy = 2441 MeV	LET = 43 MeV/(mg/cm ²)	Range = 205 μ m
b. Xeon	$_{54}\text{Xe}^{131}$	Energy = 825 MeV	LET = 59 MeV/(mg/cm ²)	Range = 66 μ m
c. Gold	$_{79}\text{Au}^{197}$	Energy = 1480 MeV	LET = 90 MeV/(mg/cm ²)	Range = 80 μ m

7.0 Record Keeping

Each irradiation shall be assigned a run number. This number will be used to correlate data from different sources.

7.1 Cyclotron Accelerator Output

The K500 Cyclotron Institute shall provide a hardcopy summary of all test runs showing key parameters such as run, date, time, flux, fluence, ion, energy, LET, and range. An output of beam diagnostics shall also be provided.

7.2 IR Output

IR shall also keep a written log of each run including run, ion, device tested, VDS and VGS biases. IR shall also record comments regarding the test including observations or deviations from test plan.

8.0 Characterizations and Verification

Characterization and Verification may be accomplished simultaneously. Characterization implies that the SOA curve is set using at least one (1) device at each insitu bias. Verification is simply an extension of the characterization, demonstrating total three (3) non-destructive devices passing at each insitu bias condition.

9.0 Test Procedure

The IR Product Engineer assigned to this test shall control the following test procedure based on Test Method 1080. IR shall be responsible to direct the ion specie, beam characteristics, insitu bias conditions and device selection.

9.1 Nominal Beam Characteristics are :
Flux = 1×10^4 (1E4) ions/cm²/sec.
Fluence = 3×10^5 (3E5) ions/cm².
Beam Diameter = 1.5 cm.
(or large enough to cover the whole die-attachment area)

9.2 Initial Starting Point : typically at VDS = Rated VDS and VGS = 0.

9.3 Irradiate the device at the selected flux and fluence.

9.4 Post irradiation, test IDSS & IGSS at VDS=80% Rated VDS and VGS up to 20 V (5 V increment).

9.5 Based on apparent pass or fail, select next operating conditions.

9.6 Repeat with new device.

10. Test Report

The Test Report shall include the following information :

- a. Device Type(s), serial numbers, wafer lot identification, date code (if applicable).
- b. Test dates and personnel names.
- c. Facility, accelerator type.
- d. Ion specie, energy, LET, range, flux and fluence.
- e. Schematic of test circuit used.
- f. Dosimeter for each ion beam used.
- g. Insitu bias conditions.
- h. Comments and observations.
- i. Pre and post electrical test results.
- j. Summary description including curves.

Appendix D

Test Circuit

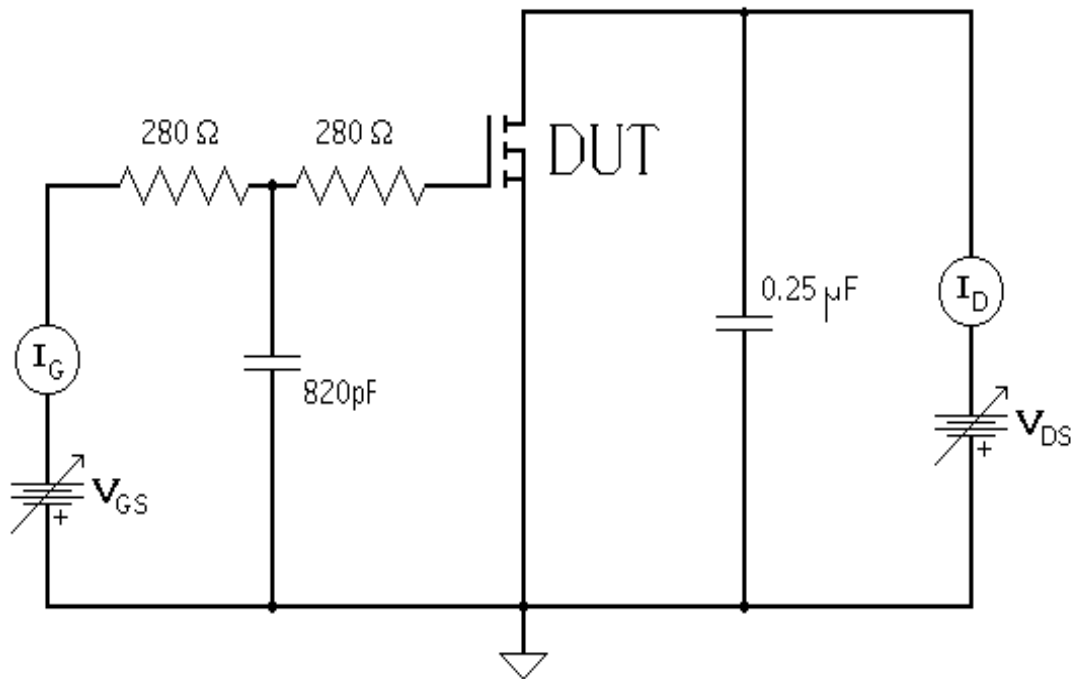
Schematic

Diagram

Reference: MIL-STD-750, Method 1080

Details of Test Method can be reviewed from DSCC Website:

http://www.dsccl.dla.mil/Downloads/MilSpec/Docs/MIL-STD-750/std750_1000.pdf



Test Circuit Schematic Diagram

Appendix E

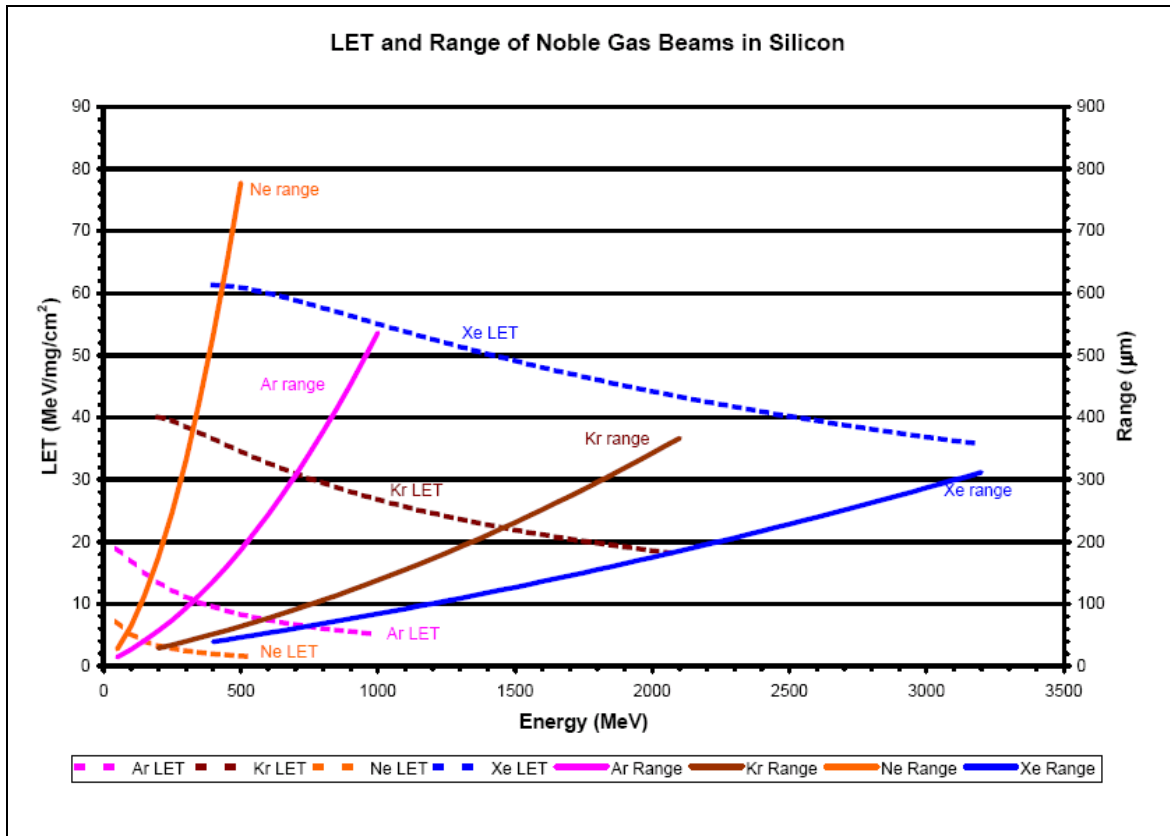
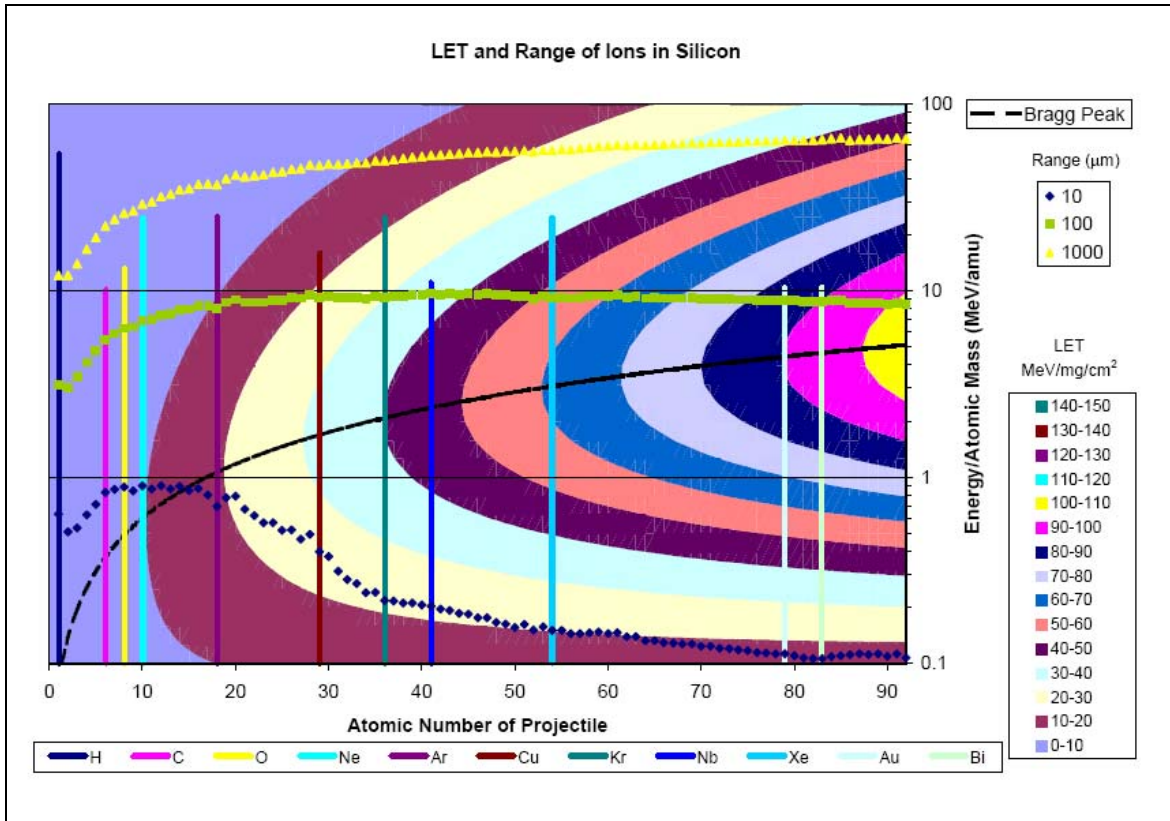
TAMU K500 Cyclotron

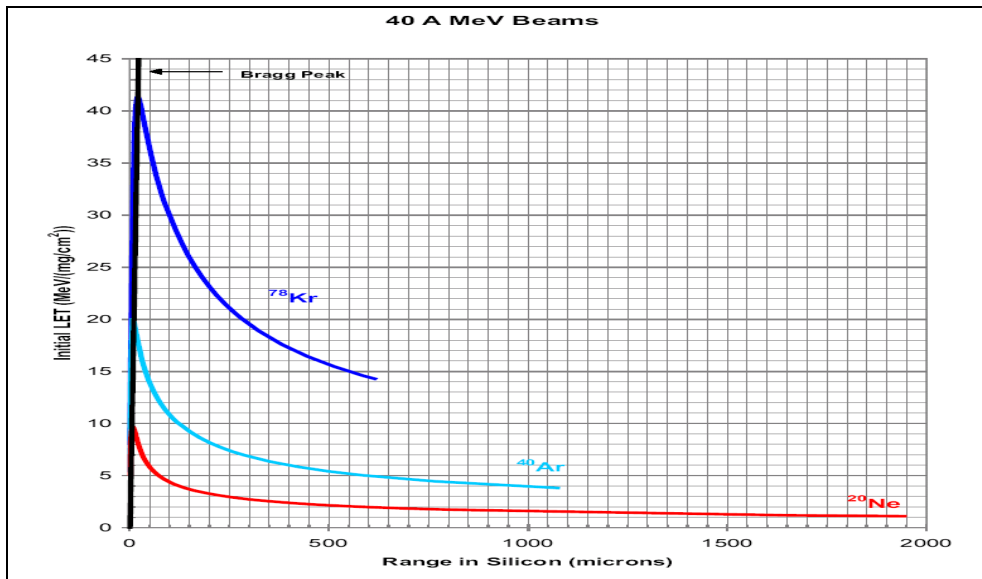
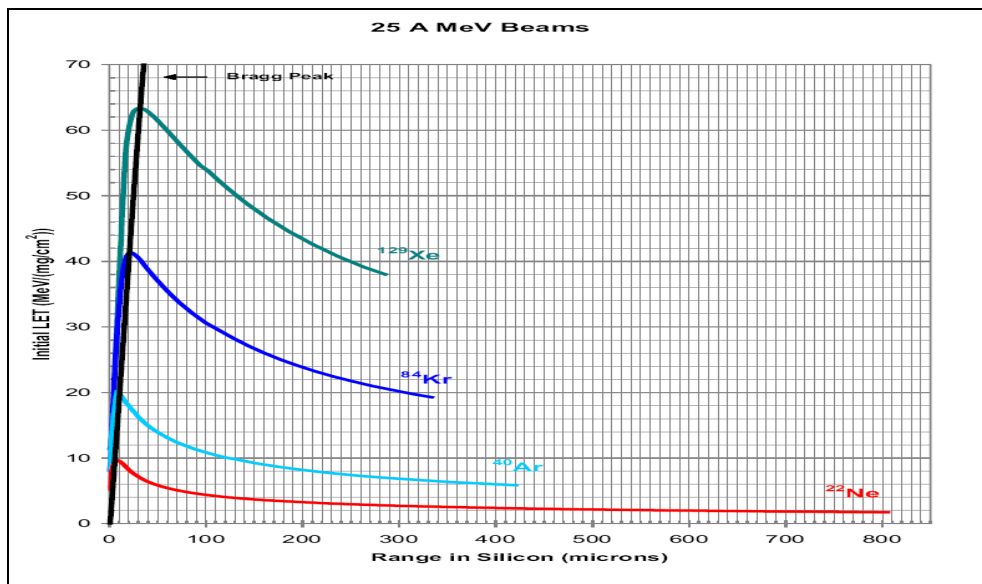
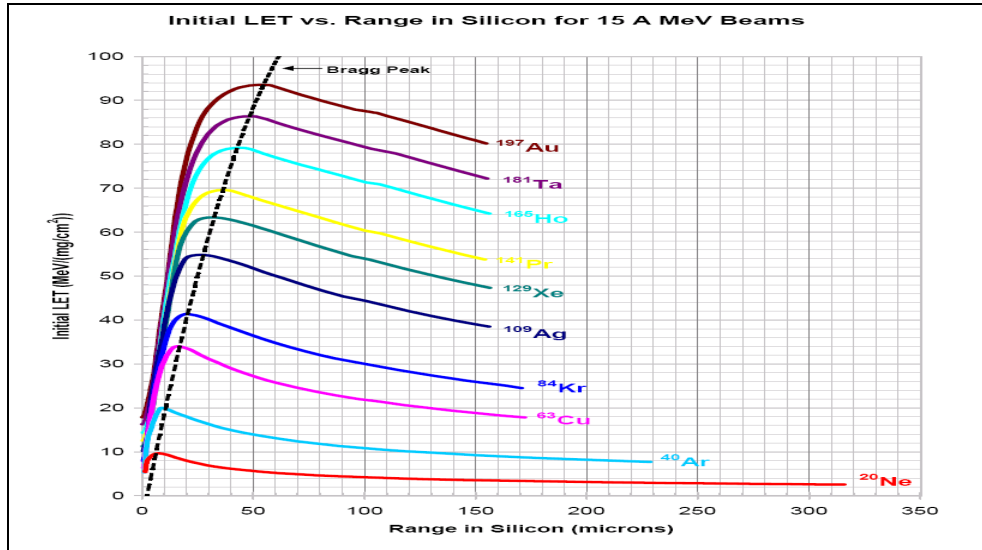
Ion Species, Surface LET and Range

 Cyclotron Institute • Texas A&M University
Radiation Effects Facility 
Available Beams

Particle	A MeV	LET _{init} (MeV/mg/cm ²)	LET _{Bragg} (MeV/mg/cm ²)	Range _{Bragg} (microns)
²⁰ Ne	15	2.5	9.6	305
⁴⁰ Ar	"	7.7	20.1	220
⁶³ Cu	"	17.8	34.0	156
⁸⁴ Kr	"	25.4	41.4	154
¹⁰⁹ Ag	"	38.5	54.8	130
¹²⁹ Xe	"	47.3	63.4	127
¹⁴¹ Pr	"	53.8	69.6	117
¹⁶⁵ Ho	"	64.3	79.2	112
¹⁸¹ Ta	"	72.2	86.4	107
¹⁹⁷ Au	"	80.2	93.5	102
²² Ne	24.8	1.7	9.7	790
⁴⁰ Ar	"	5.4	20.1	491
⁸⁴ Kr	"	19.3	41.4	315
¹²⁹ Xe	"	37.9	63.4	254
proton	40	0.012	0.58	8147
²⁰ Ne	"	1.2	9.7	1648
⁴⁰ Ar	"	3.8	20.1	1070
⁷⁸ Kr	"	14.2	41.4	601
¹⁶ O	55.1	0.59	7.4	3607
³⁶ Ar	"	3.0	20.1	1665

Cyclotron Institute • Texas A&M University
Radiation Effects Facility
Available Beams





Appendix F

Post-SEE

Electrical

Measurements

International Rectifier
SEE Test Report
August 2003 – TAMU Cyclotron

RadHard MOSFET - R6, 200V, N-channel									
		Pre - SEE Electricals Data					Post - SEE Electricals Data		
Parameter		I GSSf	I GSSr	I DSS			I GSSf	I GSSr	I DSS
Conditions		VGS=20V	VGS=-20V	VDS=160V			VGS=20V	VGS=-20V	VDS=160V
		VDS=0V	VDS=0V	VGS=0V			VDS=0V	VDS=0V	VGS=0V
Limits		100 nA Max	-100 nA Max	10 µA Max			100 nA Max	-100 nA Max	10 µA Max
Unit		nA	nA	nA			nA	nA	nA
DUT Serial									
F5	1	0.13	0.52	0.63	ER33831 (06-20-2003)	18.30	95.30	240.00	
F2	3	0.39	0.27	0.39		83.50	97.60	242.00	
F3	4	0.20	1.92	0.20		34.30	71.20	269.00	
F6	7	0.35	0.34	1.05		11.60	15.30	312.00	
F7	8	0.33	2.12	0.73		26.20	35.30	236.00	
F8	9	1.31	1.47	0.11		64.40	87.80	1190.00	
F9	10	0.23	1.52	0.75		10.50	54.90	285.00	
F10	11	0.34	2.20	0.01		31.10	67.90	257.00	
F13	15	1.58	0.50	0.19		29.60	166.00	1020.00	
F15	17	0.37	0.22	1.34		44.30	52.60	254.00	
F18	20	1.04	1.24	0.72		77.60	82.70	1120.00	
F11	23	0.41	0.42	0.90		55.10	970.00	388.00	
F19	27	0.28	2.95	0.48		59.90	77.60	450.00	
F21	29	1.17	1.12	0.71		46.80	67.60	159.00	
F22	30	0.35	0.22	0.03		24.50	43.90	220.00	
F23	31	1.00	0.41	0.05		13.66	17.10	731.00	
F25	33	0.35	0.27	0.29		71.50	83.30	109.00	
F28	36	0.32	1.52	0.69		44.70	81.60	236.00	
F29	37	0.68	0.24	0.68		0.97	90.70	62.80	
J2	49	0.03	6.36	2.15	ER33831 (08-25-2003)	6.87	9.33	587.00	
J3	54	1.94	2.66	4.62		6.14	7.88	692.00	
J4	55	0.12	6.60	2.41		1.67	2.58	563.00	
J6	60	4.56	30.45	2.35		0.83	0.98	506.00	
G5	9	2.42	4.29	3.51	ER34212 (08-25-2003)	2.24	4.29	189.00	
G9	41	18.15	11.59	4.04		5.61	8.65	516.00	
I1	11	0.72	1.45	0.28	ER34181 (08-25-2003)	0.40	0.65	820.00	
I4	17	2.17	3.59	0.84		1.34	6.24	596.00	
I9	18	3.04	3.77	0.95		3.72	7.53	269.00	